

**FEE TRANSMITTAL**

Electronic Version v08

Stylesheet Version v08.0

**Title of  
Invention****STRUCTURE AND METHOD OF MAKING STRAINED SEMICONDUCTOR  
CMOS TRANSISTORS HAVING LATTICE-MISMATCHED SOURCE AND DRAIN  
REGIONS**

Application Number :

Date :

First Named Applicant:

Huajie Chen

Attorney Docket Number:

FIS920030199US1

**TOTAL FEE AUTHORIZED \$ 1006**

Patent fees are subject to annual revisions on or about October 1st of each year.

Filing as large entity

**BASIC FILING FEE**

Fee Description	Fee Code	Amount \$	Fee Paid \$
Utility Filing Fee	1001	750	750
Subtotal For Basic Filing Fees: \$ 750			

**EXTRA CLAIM FEES**

Fee Description	Extra Claim	Fee Code	Amount \$	Fee Paid \$
Total Claims : 32	12	1202	18	216
Independent Claims : 3	0	1201	84	0
Subtotal For Extra Claims Fees: \$ 216				

**ASSIGNMENT FEES**

Fee Description	Property Number	Quantity	Fee Code	Amount \$	Fee Paid \$
Recording Each Patent Assignment Per Property Fee	00000000	1	8021	40	40
Subtotal For Additional Fees: \$40					

**AUTHORIZED BILLING INFORMATION****The commissioner is hereby authorized to charge indicated fees and credit any  
overpayments to:**

Deposit account number:

090458

Deposit name:

International Business Machines Corporation

Deposit authorized name:

H. Daniel Schnurmann

Signature:

H. Daniel Schnurman

Date (YYYYMMDD):

2003-08-04

Charge Any Additional Fee Required Under 37 C.F.R. Sections 1.16 and 1.17.